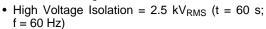


Power MOSFET

PRODUCT SUMMA	RODUCT SUMMARY			
V _{DS} (V)	- 60)		
$R_{DS(on)}\left(\Omega\right)$	V _{GS} = - 10 V	0.053		
Q _g (Max.) (nC)	12			
Q _{gs} (nC)	3.8			
Q _{gd} (nC)	5.1			
Configuration	Sing	le		

FEATURES

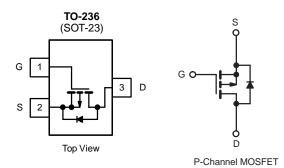
Isolated Package





RoHS COMPLIANT

- Sink to Lead Creepage Distance = 4.8 mm
- P-Channel
- 175 °C Operating Temperature
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available



ABSOLUTE MAXIMUM RATINGS T	_C = 25 °C, u	nless otherw	ise noted			
PARAMETER			SYMBOL	LIMIT	UNIT	
Drain-Source Voltage			V _{DS}	- 60	V	
Gate-Source Voltage			V_{GS}	± 20	V	
Continuous Drain Current	V at 10 V	$T_{\rm C} = 25 ^{\circ}{\rm C}$ $T_{\rm C} = 100 ^{\circ}{\rm C}$	ا ا	- 5.2		
Continuous Diain Current	VGS at - 10 V	T _C = 100 °C		- 3.8	Α	
Pulsed Drain Current ^a			I_{DM}	- 21		
Linear Derating Factor				0.18	W/°C	
Single Pulse Avalanche Energy ^b			E _{AS}	120	mJ	
Repetitive Avalanche Currenta			I _{AR}	- 5.2	Α	
Repetitive Avalanche Energy ^a			E _{AR}	2.7	mJ	
Maximum Power Dissipation T _C = 25 °C		P_{D}	27	W		
Peak Diode Recovery dV/dtc			dV/dt	- 4.5	V/ns	
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 175	°C	
Soldering Recommendations (Peak Temperature)	for	10 s		300 ^d	C	
Mounting Torque	6-32 or M3 screw		·	10	lbf ⋅ in	
Mounting Torque				1.1	N⋅m	

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11). b. V_{DD} = 25 V, starting T_J = 25 °C, L = 5.0 mH, R_G = 25 Ω , I_{AS} = 5.3 A (see fig. 12). c. I_{SD} < 6.7 A, dI/dt < 90 A/µs, V_{DD} \leq V_{DS} , V_{DS} \leq 175 °C.

- d. 1.6 mm from case.



THERMAL RESISTANCE RAT	FINGS			
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	-	5.5	C/VV

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		- 60	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	e to 25 °C, I _D = - 1 mA	-	- 0.060	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	V _{GS} , I _D = - 250 μA	- 1.0	-	- 3.0	V
Gate-Source Leakage	I _{GSS}	,	V _{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =	V _{DS} = - 60 V, V _{GS} = 0 V		-	- 100	
		V _{DS} = - 60	V _{GS} = 0 V, T _J = 150 °C	-	-	- 500	μA
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 3.2 A ^b	-	0.053	0.059	Ω
Forward Transconductance	9 _{fs}	V _{DS} =	- 25 V, I _D = - 3.2 A ^b	1.6	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V,		-	270	-	-
Output Capacitance	C _{oss}		$V_{DS} = -25 \text{ V},$		170	-	
Reverse Transfer Capacitance	C _{rss}	f = 1	0 MHz, see fig. 5	-	31	-	pF
Drain to Sink Capacitance	С		f = 1.0 MHz		12	-	1
Total Gate Charge	Qg			-	-	12	
Gate-Source Charge	Q _{gs}	V _{GS} = - 10 V	$I_D = -4.7 \text{ A}, V_{DS} = -48 \text{ V},$ see fig. 6 and 13 ^b	-	-	3.8	nC
Gate-Drain Charge	Q _{gd}	1		-	-	5.1	
Turn-On Delay Time	t _{d(on)}	$V_{DD} = -30 \text{ V}, I_{D} = -4.7 \text{ A},$ $R_{G} = 24 \Omega, R_{D} = 4.0 \Omega,$ see fig. 10^{b}		-	11	-	- ns
Rise Time	t _r			-	63	-	
Turn-Off Delay Time	t _{d(off)}			-	9.6	-	
Fall Time	t _f			-	31	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	
Internal Source Inductance	L _S			-	7.5	-	- nH
Drain-Source Body Diode Characteristic	s						ı
Continuous Source-Drain Diode Current	I _S	showing the	MOSFET symbol showing the		-	- 5.2	А
Pulsed Diode Forward Current ^a	I _{SM}	integral reverse p - n junction diode		-	-	- 21	^
Body Diode Voltage	V_{SD}	$T_J = 25 ^{\circ}\text{C}, I_S = -5.2 \text{A}, V_{GS} = 0 \text{V}^{\text{b}}$		-	-	- 5 .5	V
Body Diode Reverse Recovery Time	t _{rr}	$T_J = 25 ^{\circ}\text{C}, \ I_F = -4.7 \text{A}, \ \text{dI/dt} = 100 \text{A/}\mu\text{s}^b$		-	80	160	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	0.096	0.19	μC
Forward Turn-On Time	t _{on}	Intrinsic tu	on is don	ninated by	L _S and I	_D)	

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300~\mu s;$ duty cycle $\leq 2~\%.$



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

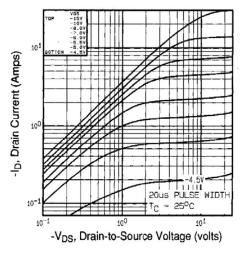


Fig. 1 - Typical Output Characteristics, T_C= 25 °C

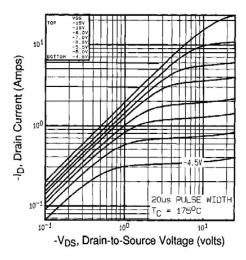


Fig. 2 - Typical Output Characteristics, T_{C} = 175 °C

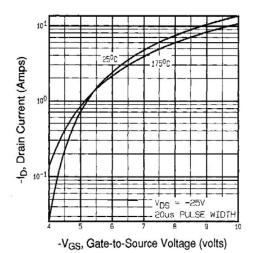


Fig. 3 - Typical Transfer Characteristics

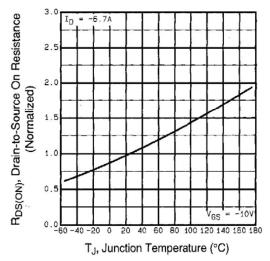


Fig. 4 - Normalized On-Resistance vs. Temperature

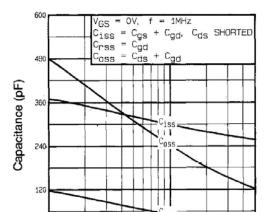


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

-V_{DS}, Drain-to-Source Voltage (volts)

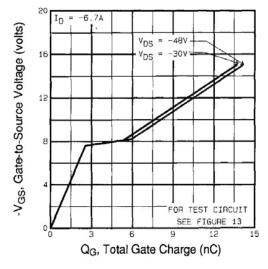


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

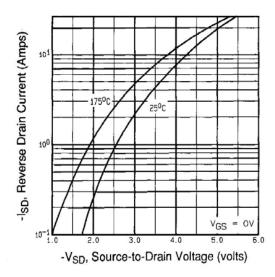


Fig. 7 - Typical Source-Drain Diode Forward Voltage

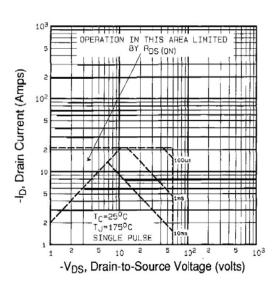


Fig. 8 - Maximum Safe Operating Area



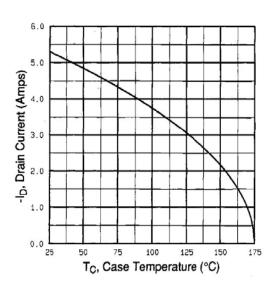


Fig. 9 - Maximum Drain Current vs. Case Temperature

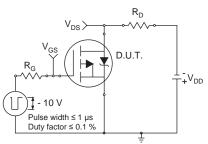


Fig. 10a - Switching Time Test Circuit

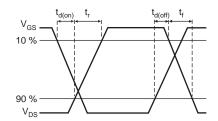


Fig. 10b - Switching Time Waveforms

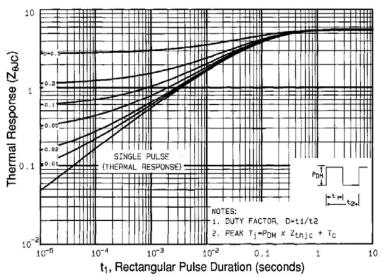


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

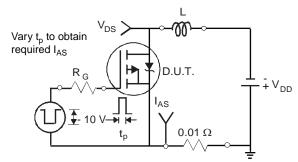


Fig. 12a - Unclamped Inductive Test Circuit

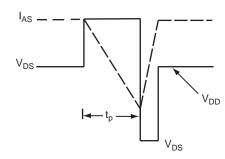


Fig. 12b - Unclamped Inductive Waveforms

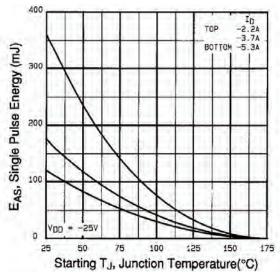


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

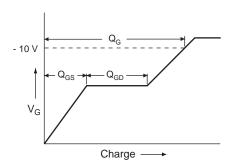


Fig. 13a - Basic Gate Charge Waveform

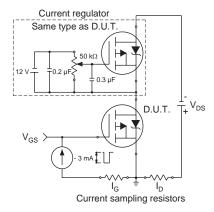
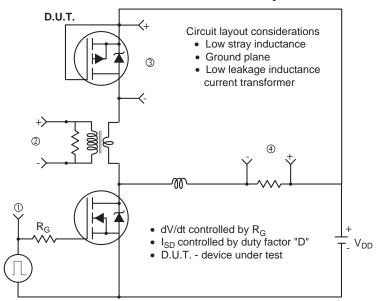
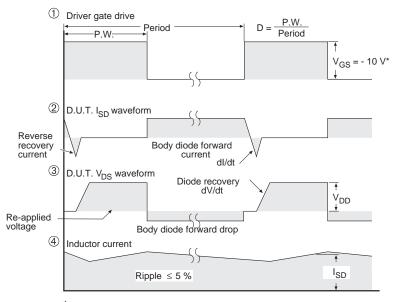


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



• Compliment N-Channel of D.U.T. for driver

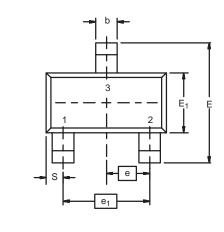


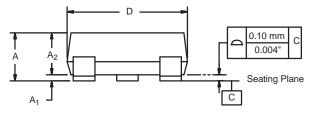
* $V_{GS} = -5 \text{ V}$ for logic level and -3 V drive devices

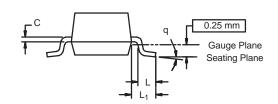
Fig. 14 - For P-Channel



SOT-23 (TO-236): 3-LEAD







Dim	MILLIM	IETERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95	0.95 BSC		0.0374 Ref	
e ₁	1.90	1.90 BSC		8 Ref	
L	0.40	0.60	0.016	0.024	
L ₁	0.64	0.64 Ref		Ref	
S	0.50 Ref		0.020) Ref	
q	3°	8°	3°	8°	

DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)





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